

Application No. 09/002,007
Attorney's Docket No. 015290-238

E1 end

a plasma generating device, the system of etching agents being nitrogen-free and including one or more fluorine-containing compounds, chlorine and an optional inert carrier gas.

E2
13 11. (Amended) A method for substantially preserving a photoresist while removing exposed areas of an organic ARC during the manufacturing of an integrated circuit comprising exposing the ARC to an oxygen-free system of etching agents in an ionized state in a reaction chamber of a plasma generating device, the system of etching agents being nitrogen-free and including one or more fluorine-containing compounds, an inert carrier gas and chlorine.

E3
13 18 12. (Amended) A process for etching a pattern of exposed areas of an organic ARC, comprising exposing the ARC to an oxygen-free system of etching agents in an ionized state in a reaction chamber of a plasma generating device, the system of etching agents being nitrogen-free and including one or more fluorine-containing compounds, chlorine, and an inert carrier gas, wherein a photoresist layer forming the pattern of exposed area is disposed on the organic ARC, and wherein the organic ARC is selectively etched and the photoresist is substantially preserved such that lateral degradation of the photoresist layer forming the pattern of exposed areas is substantially prevented.